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(54) **METHOD FOR MAKING ELECTRODE PAIRS**

(75) Inventors: **Avto Tavkhelidze**, Tbilisi (GE); **Leri Tsakadze**, Tbilisi (GE); **Givi Skhiladze**, Tbilisi (GE); **Isaiah Watas Cox**, London (GB)

(73) Assignee: **Borealis Technical Limited**, Gibraltar

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(51) **Int. Cl.**⁷ **H01L 21/20**

(52) **U.S. Cl.** **438/380**; 438/979

(58) **Field of Search** 438/380, 133, 438/141, 142, 328, 553, 557, 979, 983

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Primary Examiner—David Nhu

(57) **ABSTRACT**

The present invention is a method for introducing a low work function material into a pair of matched electrodes. The method involves fabricating a composite of two electrodes and a low work function material, and treating the composite so that it splits to give a pair of matched electrodes.

22 Claims, 6 Drawing Sheets

